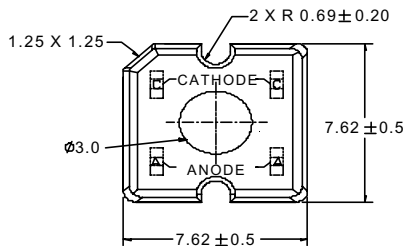


BVZ-916GE4

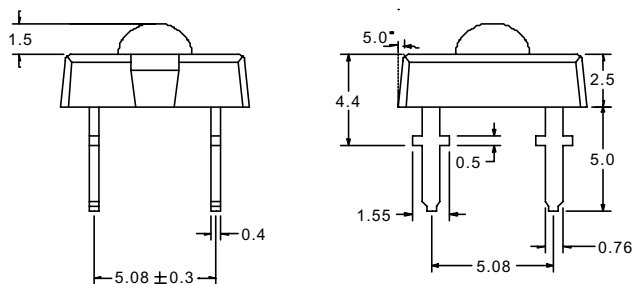
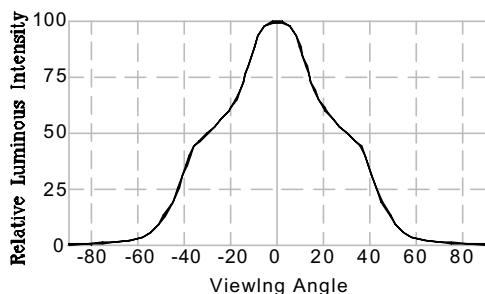
PACKAGE CONFIGURATION

DESCRIPTION

Dice Material : InGaN/SiC Green
Light Color : Green Color
Lens Color : Water Transparent



RADIATION PATTERN



Tolerance ± 0.25 mm

ABSOLUTE MAXIMUM RATINGS AT Ta = 25 °C

PARAMETER	MAX.	UNIT
Power Dissipation	260	mW
Continuous Forward Current	50	mA
Peak Forward Current (1/10 Duty Cycle , 0.1ms Pulse Width)	100	mA
Reverse Voltage	5	V
Derating Linear From 50°C	0.7	mA/°C
Operating Temperature Range	-40 to + 100	°C
Storage Temperature Range	-55 to + 100	°C
LED Junction Temperature	125	°C
Soldering Preheat Temperature	100 °C for 30 seconds	
Lead Solder Temperature (1.5mm Below Seating Plane)	260 °C for 5 seconds	

ELECTRICAL / OPTICAL CHARACTERISTICS AT Ta = 25 °C

SYMBOL	PARAMETER	TEST COND.	MIN.	TYP.	MAX.	UNIT
V _F	Forward Voltage	I _F = 50mA		4.5	5.2	V
I _R	Reverse Current	V _R = 5V			10	μA
λ _p	Peak Emission Wavelength	I _F = 50mA		520		nm
λ _d	Dominant Wavelength	I _F = 50mA		525		nm
2θ _{1/2}	Viewing Angle	I _F = 50mA		60		Deg
I _V / Φ _V	Luminous Intensity / Total Flux			0.8		cd/lm
R _{θ j-pin}	Thermal Resistance			125		°C/W

BIN GRADE LIMITS (I F = 50 mA) Total Flux / lm

Bin	C	D	E	F	G	H	I	J
Min.	1.3	1.7	2.2	2.8	3.6	4.7	6.0	7.8
Max.	1.7	2.2	2.8	3.6	4.7	6.0	7.8	10.0

Tolerance ± 15%lm

*Bright View reserves the rights to alter specifications and remove availability of products at any time without notice.

*Dominant Wavelength, λ_d is according to CIE Chromaticity Diagram base on color of the device.

*θ_{1/2} is the off-axis angle where the luminous intensity is one half the on-axis intensity.

*These products are sensitive to static electricity. Caution must be taken strictly to avoid static electricity.



InGaN / SiC Green LED

TYPICAL ELECTRICAL/OPTICAL CHARACTERISTIC CURVES

FIG. 1 Forward Current Vs. Forward Voltage

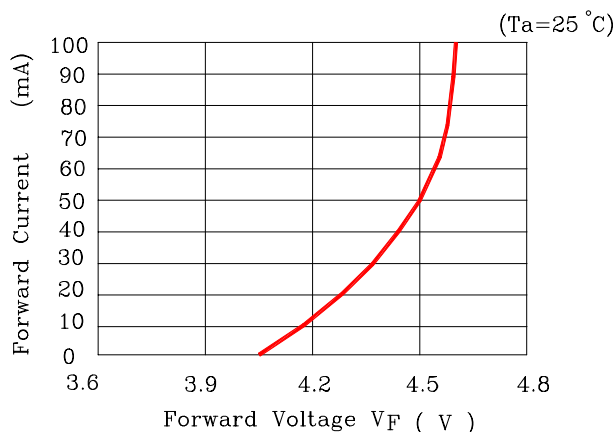


FIG. 2 Relative Total Flux Vs. Forward Current

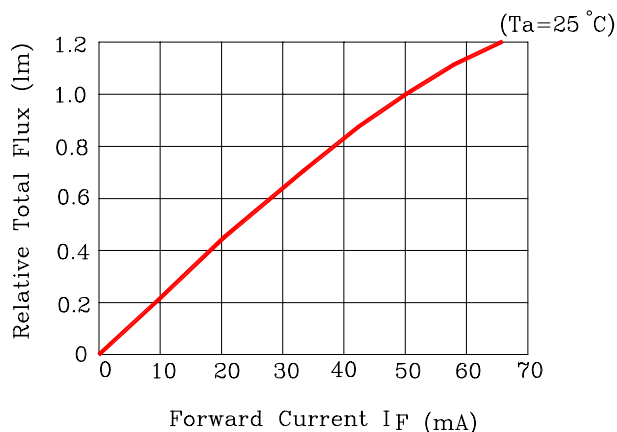


FIG. 3 Forward Voltage VS. Temperature

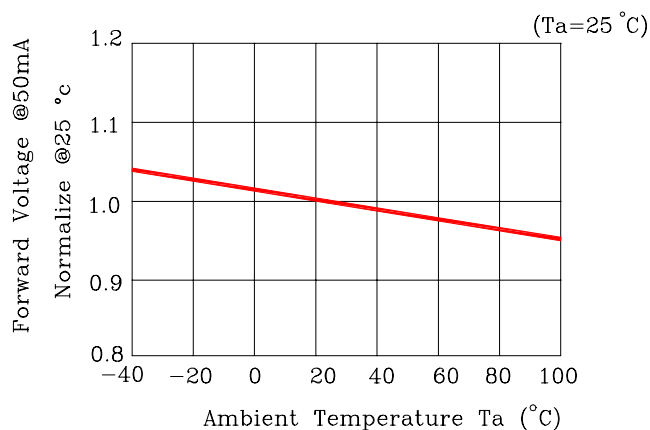


FIG. 4 Relative Total Flux vs. Temperature

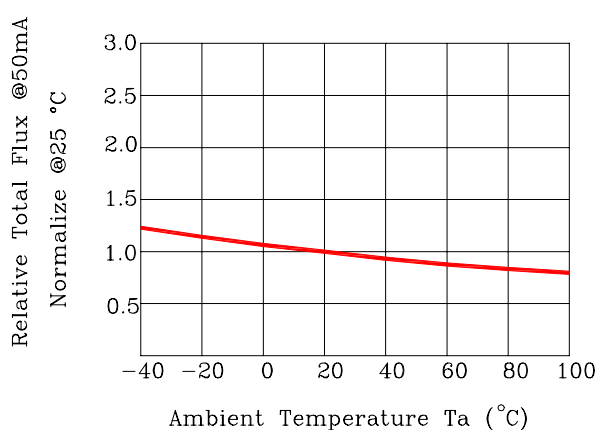


FIG. 5 Relative Intensity vs. Wavelength (λ_p)

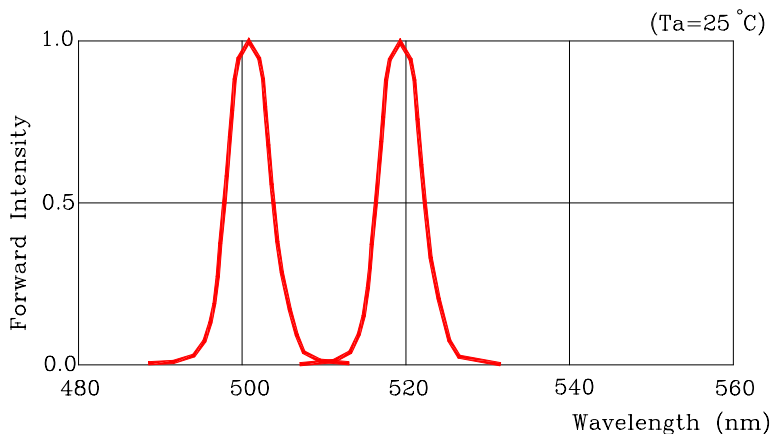
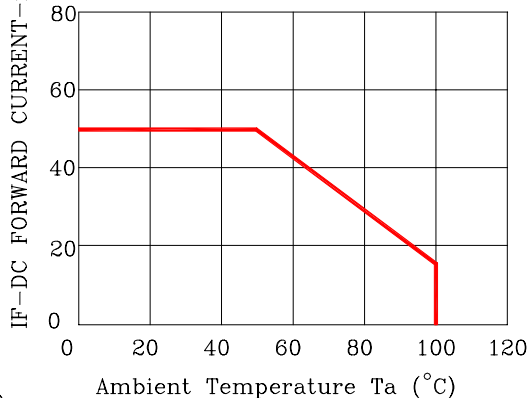


FIG. 6 Maximum Forward Current vs. Ambient Temperature. Derating Based on $T_{MAX}=125^{\circ}C$





靜電防治

These products are Gallium Nitride(GaN) or Indium Gallium Nitride(InGaN) light emitting diodes(LEDs). There are extremely sensitive to static electricity ESD damage. The user must take absolutely secure countermeasures against static electricity and surge when handling products.

顯明 LED 晶片材質為 Gallium Nitride(GaN)或 Indium Gallium Nitride(InGaN) ，此材質對於靜電極為敏感，十分容易受靜電衝擊而產生破壞，使用者接觸產品時必需做好對靜電衝擊之防護措施。

Bright View Blue, Green are GaN/ Sic or InGaN/ Sic materials are ESD classified, any manufacturing or workstations where GaN/ Sic or InGaN/ Sic devices are handled should be rated at "Class 2" 100V maximum.

顯明之藍、綠光晶片材質為 GaN/Sic 或 InGaN/ Sic ，此材質屬 ESD 規範，任何 GaN/ Sic 或 InGaN/ Sic 產品所會被接觸的製造或工作站必須控制在 100V 以下。

Proper grounding of products (via 1M Ω), use of conductive mat, semiconductive working uniform and shoes, and semiconductive containers are considered to be effective as countermeasures against static electricity and surge.

適當的產品接地（1M Ω ）與使用導電桌墊，並評估考慮穿著防靜電工作服、防靜電鞋與防靜電盒來有效地防制靜電之衝擊。

An ionizer is recommended to be used in the facility or environment where static electricity may be generated easily, and soldering iron with a grounded tip is also recommended.

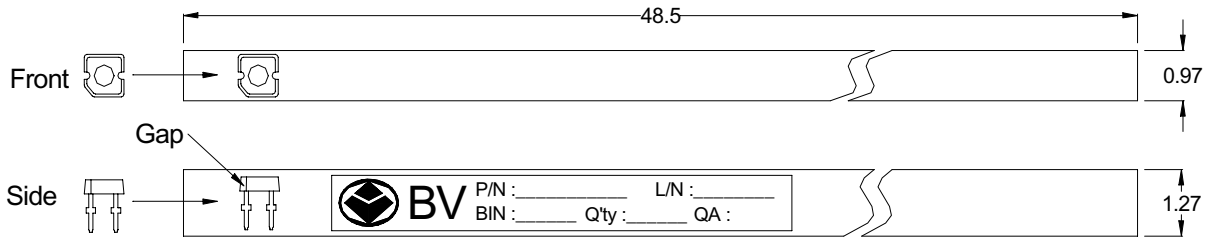
建議對於工廠設施與環境中容易產生靜電的地點使用離子風扇吹拂，且也建議使用有接地功能的烙鐵進行焊接。

To install a protection device, in the LED driving circuit, which does not exceed the max rating for surge current during on/off switching.

在驅動 LED 的電路上設置保護裝置，使其當開閉時的瞬間電流不會超出最大電壓值。



SUPER FLUX PACKING



Tube
Dimension(cm): 1.27* 0.97* 48.5
60PCS / Tube



BOX
Dimension(cm): 10.5 * 13.5 * 50.5
100 Tubes / Box
Box : 6,000PCS

Bright View Electronics Co.,Ltd.

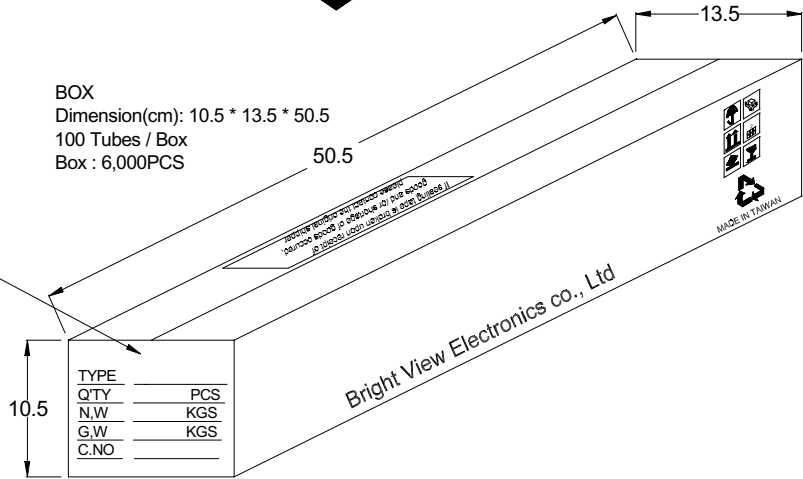
PART NO.: BVZ-91XXXX

LOT NO.:

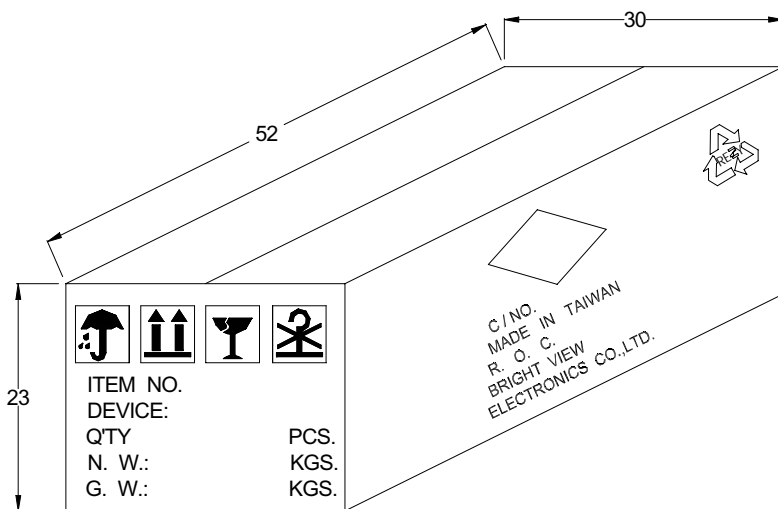
GRADE: X- Δ - ■

Q'ty pcs QA

X: Bin grade
Δ: Wavelength
■: Vf



CARTON
Dimension(cm): 23*30*52



4 Boxes / Carton
Total : 24,000PCS